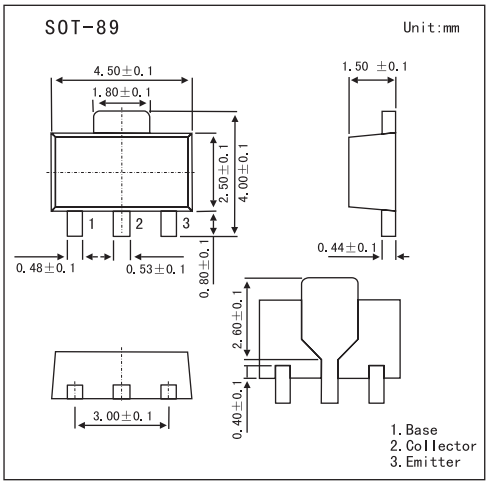
PNP Epitaxial Planar Silicon

2SA1766



■ Features

- Adoption of FBET, MBIT processes.
- High DC current gain (h_{FE}=500 to 1200).
- Large current capacity.
- Low collector-to-emitter saturation voltage.
- High V_{EBO}.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-30	V
Collector-emitter voltage	V_{CEO}	-25	V
Emitter-base voltage	V_{EBO}	-15	V
Collector current	I_C	-300	mA
Collector current (pulse)	I_{CP}	-500	mA
Base current	I_B	-60	mA
Collector dissipation	P_C	1.3	mW
Jumction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = -20V , I_E = 0			-0.1	μA
Emitter cutoff current	I_{EBO}	V_{EB} = -10V , I_C = 0			-0.1	μA
DC current Gain	h_{FE}	V_{CE} = -5V , I_C = -10mA	500	800	1200	
Gain bandwidth product	f_T	V_{CE} = -10V , I_C = -10mA		100		MHz
Common base output capacitance	Cob	V_{CB} = -10V , f = 1MHz		12		pF
Collector-to-emitter saturation voltage	$V_{CE(sat)}$	I_C = -200mA , I_B =-4mA		-0.12	-0.5	V
Base-to-emitter saturation voltage	$V_{BE(sat)}$	I_C = -200A , I_B =-4mA		-0.77	-1.1	V
Collector-to-base breakdown voltage	$V_{(BR)CBO}$	I_C = -10μA , I_E = 0	-30			V
Collector-to-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = -1mA , R_{BE} = ∞	-25			V
Emitter-to-base breakdown voltage	$V_{(BR)EBO}$	I_E = -10μA , I_C = 0	-15			V

■ Marking

Marking	AL